

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a TO220F "full pack" plastic package intended for use in applications requiring good bidirectional blocking voltage and high surge current capability and high junction temperature capability ($T_{j(max)} = 150\text{ °C}$).

2. Features and benefits

- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- Good blocking voltage capability
- Very high surge current capability
- High thermal cycling performance
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_h \leq 68\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	20	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig 4 ; Fig 5	-	-	225	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$	-	-	248	A
T_j	junction temperature		-	-	150	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7	-	-	6.2	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9	-	-	40	mA
V_T	on-state voltage	$I_T = 20\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	-	1.6	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 150\text{ °C}$; exponential waveform; gate open circuit	300	-	-	V/ μ s

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
TYN20X-800TF	TO220F	TYN20X-800TFQ	Tube	50	SOT186A	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes	
	Assembly factory: d	Assembly factory: A
TYN20X-800TF	TYN20X 800TF PJdxxxx xx	TYN20X 800TF PJAxxxx xx

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
V_{RRM}	repetitive peak reverse voltage		-	800	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_h \leq 68\text{ °C}$	-	12.7	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_h \leq 68\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	20	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig 4 ; Fig 5	-	225	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$	-	248	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	254	A ² s
di_T/dt	rate of rise of on-state current	$I_G = 20\text{ mA}$	-	125	A/ μ s
I_{GM}	peak gate current		-	4	A
V_{GM}	peak gate voltage		-	5	V
P_{GM}	peak gate power		-	20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
T_{stg}	storage temperature		-40	150	°C
T_j	junction temperature		-	150	°C

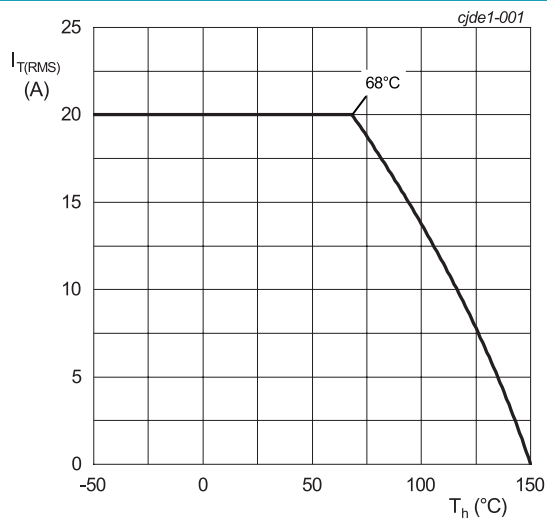
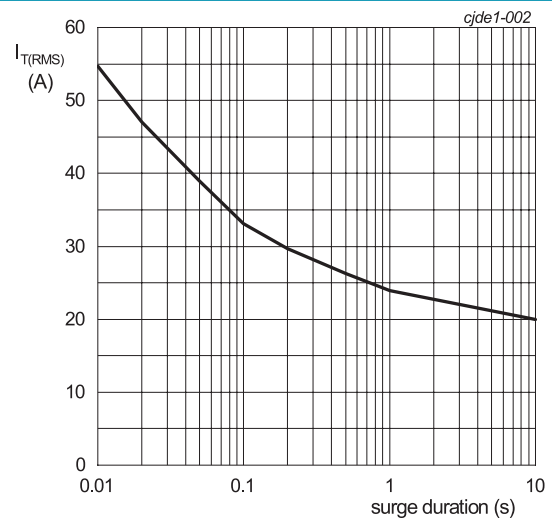
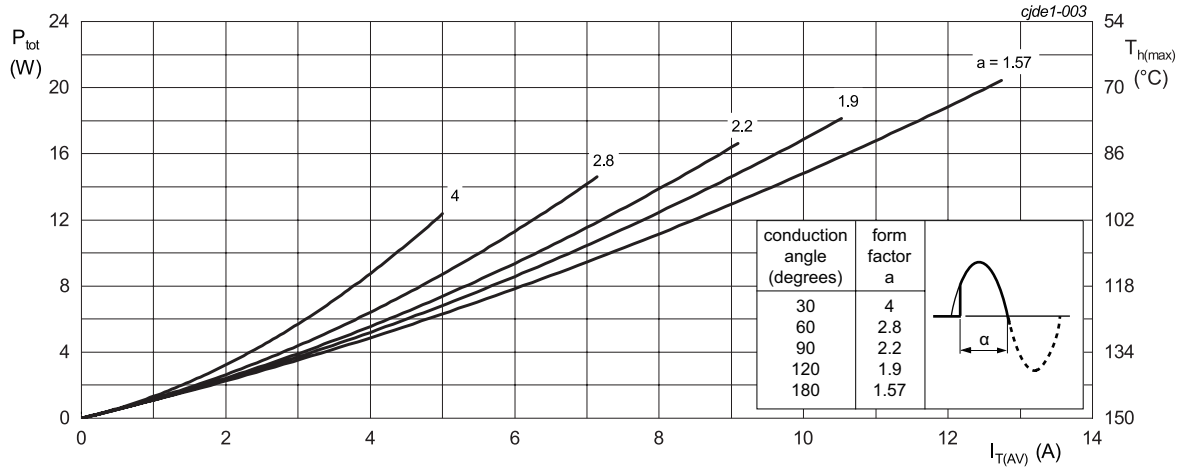


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values



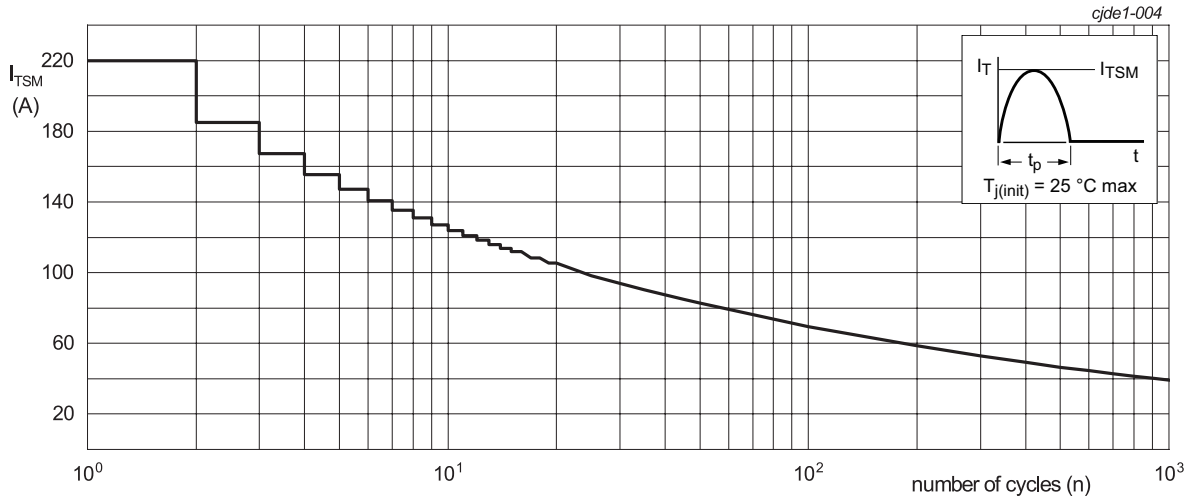
$f = 50\text{ Hz}$; $T_h = 68\text{ °C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values



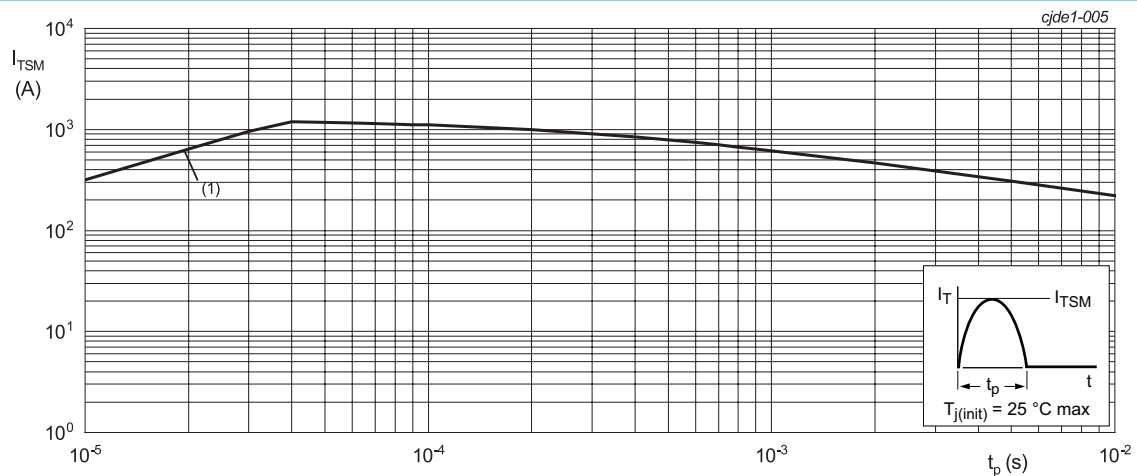
α = conduction angle
 a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



$f = 50 \text{ Hz}$

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



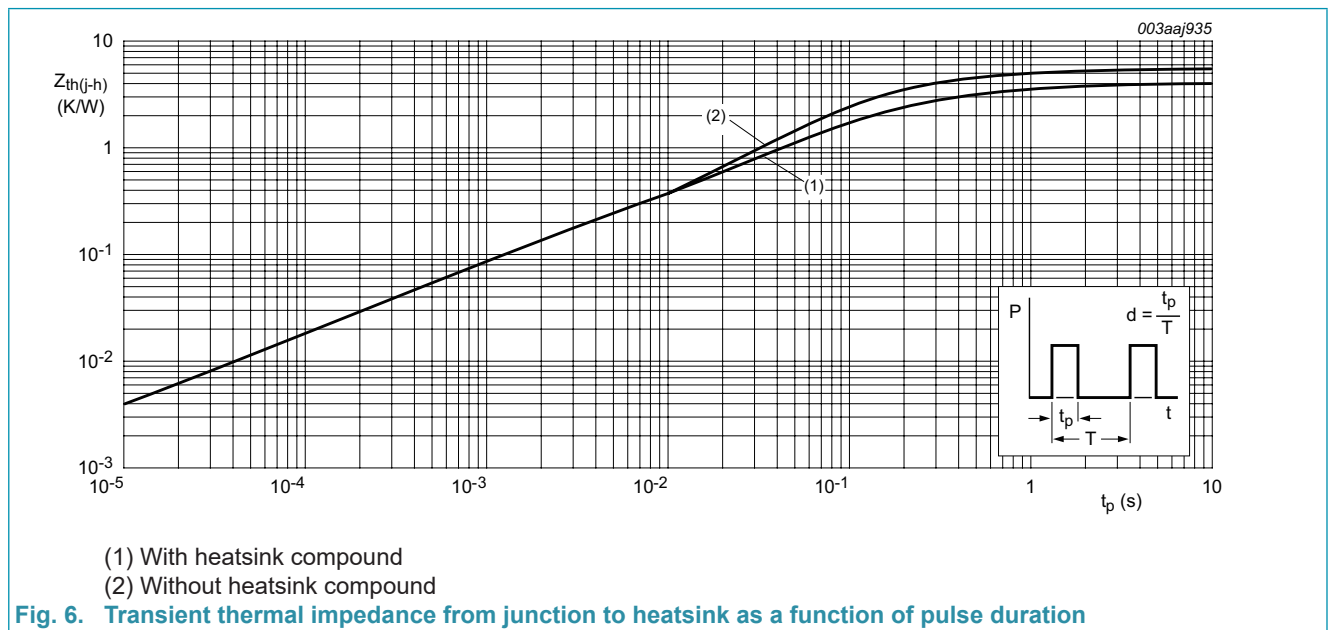
$t_p \leq 10 \text{ ms}$
 (1) di_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 6	-	-	4	K/W
		without heatsink compound	-	-	5.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	f = 1 MHz; T _h = 25 °C; from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	-	6.2	mA
I_L	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	60	mA
I_H	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	-	40	mA
V_T	on-state voltage	$I_T = 20\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	-	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 11	-	0.75	1	V
		$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 150\text{ }^\circ\text{C}$	0.25	0.4	-	V
I_D	off-state current	$V_D = 800\text{ V}; T_j = 150\text{ }^\circ\text{C}$	-	-	1	mA
I_R	reverse current	$V_D = 800\text{ V}; T_j = 150\text{ }^\circ\text{C}$	-	-	1	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}; T_j = 150\text{ }^\circ\text{C}$; exponential waveform; gate open circuit	300	-	-	V/ μs
		$V_{DM} = 536\text{ V}; R_{GK} = 100\text{ }\Omega; T_j = 150\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform	500	-	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 20\text{ A}; V_D = 800\text{ V}; I_G = 100\text{ mA}$; $(dI_G/dt)_M = 5\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}$	-	2	-	μs
t_q	commutated turn-off time	$I_{TM} = 2\text{ A}; t_p = 50\text{ }\mu\text{s}; dV_D/dt = 5\text{ V}/\mu\text{s}; dI/dt = 30\text{ A}/\mu\text{s}$	-	-	12	μs

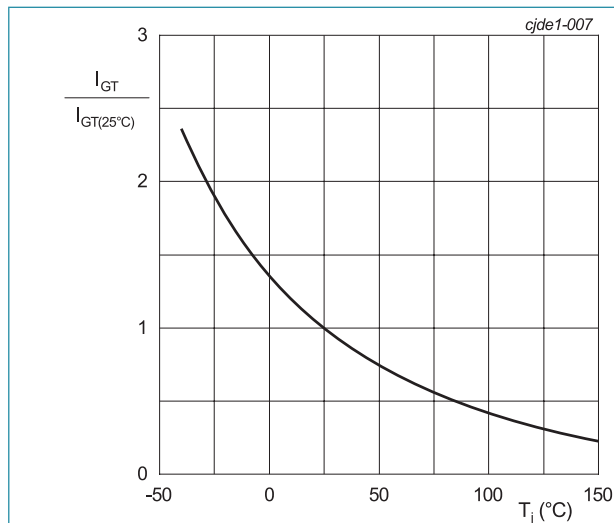


Fig. 7. Normalized gate trigger current as a function of junction temperature

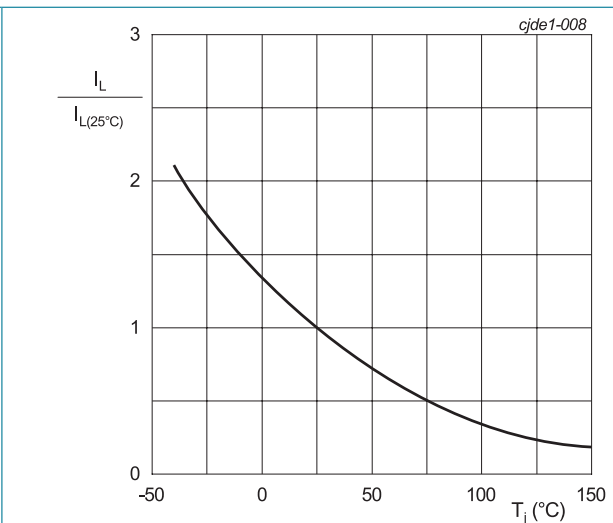


Fig. 8. Normalized latching current as a function of junction temperature

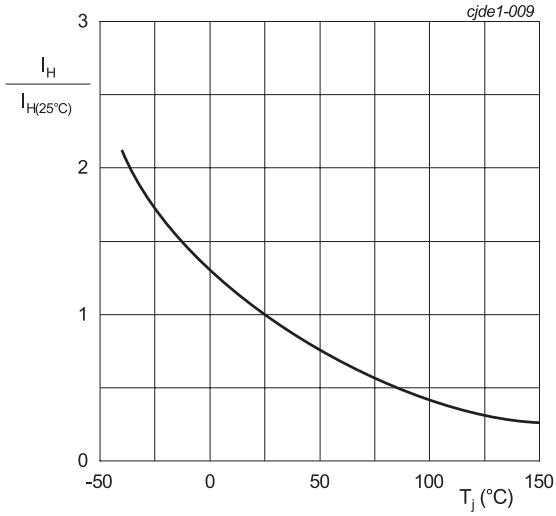
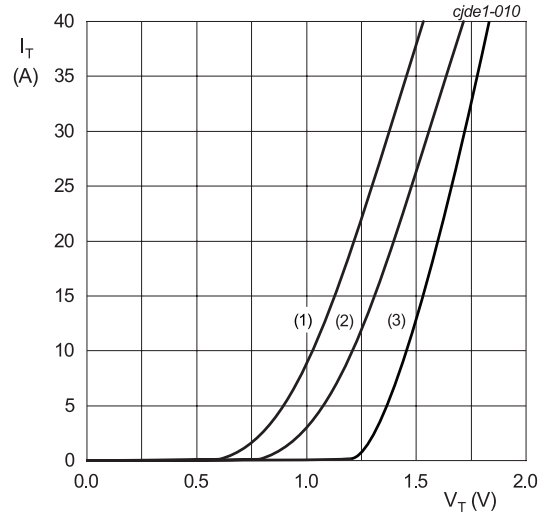


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.041 \text{ V}$; $R_s = 0.0179 \Omega$
 (1) $T_j = 150 \text{ }^\circ\text{C}$; typical values
 (2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values
 (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

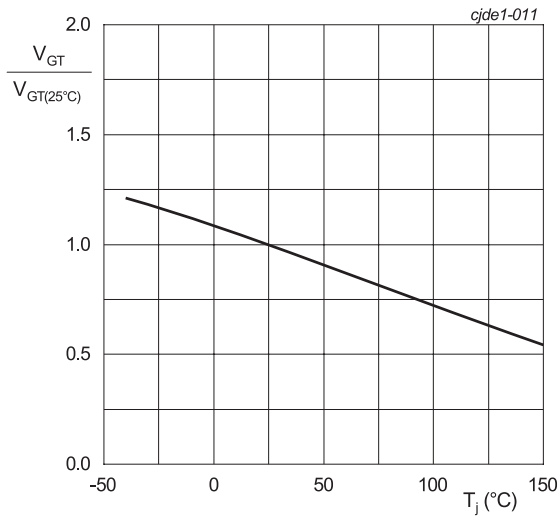


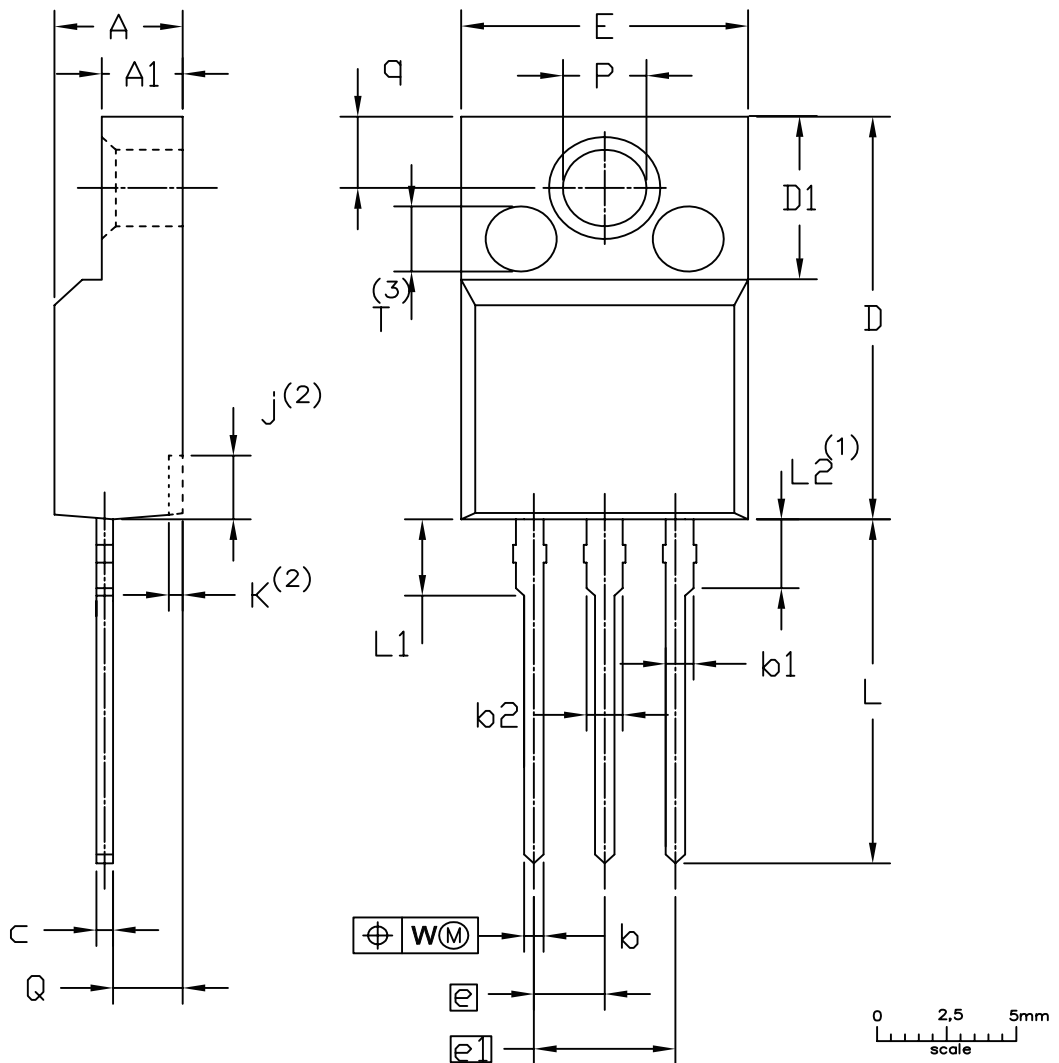
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

Assembly factory: d & A

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"

SOT186A



UNIT	A	A ₁	b	b ₁	b ₂	c	D	D ₁	E	e	e ₁	j ⁽²⁾	k ⁽²⁾	L	L ₁	L ₂ ⁽¹⁾ max.	P	Q	q	W	T ⁽³⁾
mm	4.6	2.9	0.9	1.1	1.4	0.7	15.8	6.5	10.3	2.54	5.08	2.7	0.6	14.4	3.30	3	3.2	2.6	3.0	0.4	2.5
	4.0	2.5	0.7	0.9	1.0	0.4	15.2	6.3	9.7			1.7	0.4	13.5	2.79		3.0	2.3	2.6		

Notes

- Terminal dimensions within this zone are uncontrolled
- Dot lines area designs may vary
- Eject pin mark is for reference only

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT186A		3 LEADS TO220F			2013-11-14

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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